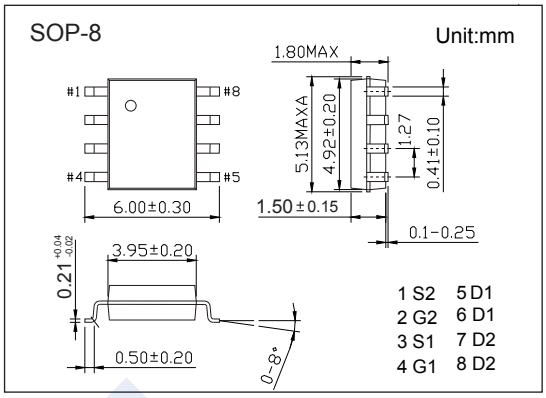
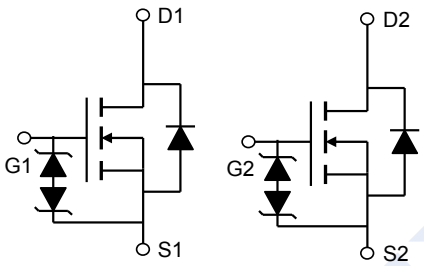
Dual N-Channel MOSFET

AO4818 (KO4818)



■ Features

- $V_{DS\ (V)}$ = 30V
- I_D = 8A (V_{GS} = 10V)
- $R_{DS(ON)}$ < 19mΩ (V_{GS} = 10V)
- $R_{DS(ON)}$ < 23mΩ (V_{GS} = 4.5V)
- ESD Rating: 2KV HBM



■ Absolute Maximum Ratings Ta = 25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	
Continuous Drain Current	T_A=25℃	I_D	8	A
	T_A=70℃		6.5	
Pulsed Drain Current		I_{DM}	48	
Avalanche Current		I_{AS}, I_{AR}	19	
Avalanche Energy	L=0.1mH	E_{AS}, E_{AR}	18	mJ
Power Dissipation	T_A=25℃	P_D	2	W
	T_A=70℃		1.3	
Thermal Resistance.Junction- to-Ambient	t ≤ 10s	R_{thJA}	62.5	℃/W
	Steady-State		90	
Thermal Resistance.Junction- to-Lead		R_{thJL}	40	
Junction Temperature		T_J	150	℃
Storage Temperature Range		T_{stg}	-55 to 150	

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■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	V_{DSS}	I_D=250μA, V_{GS}=0V	30			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V, V_{GS}=0V			1	uA
		V_{DS}=30V, V_{GS}=0V, T_J=55℃			5	
Gate-Body Leakage Current	I_{GSS}	V_{DS}=0V, V_{GS}=±20V			±10	uA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS} , I_D=250uA	1.2		2.4	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	V_{GS}=10V, I_D=8A			19	mΩ
		V_{GS}=10V, I_D=8A T_J=125℃			25	
		V_{GS}=4.5V, I_D=4A			23	
On State Drain Current	$I_{D(ON)}$	V_{GS}=10V, V_{DS}=5V	30			A
Forward Transconductance	g_{FS}	V_{DS}=5V, I_D=8A		30		S
Input Capacitance	C_{iss}	V_{GS}=0V, V_{DS}=15V, f=1MHz	600		888	pF
Output Capacitance	C_{oss}		77		145	
Reverse Transfer Capacitance	C_{rss}		50		115	
Gate Resistance	R_g	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.5		1.7	Ω
Total Gate Charge (10V)	Q_g	V_{GS}=10V, V_{DS}=15V, I_D=8A	12		18	nC
Total Gate Charge (4.5V)			6		9	
Gate Source Charge	Q_{gs}			2.5		
Gate Drain Charge	Q_{gd}			3		
Turn-On DelayTime	$t_{d(on)}$	V_{GS}=10V, V_{DS}=15V, R_L=1.8Ω, R_{GEN}=3Ω		5		ns
Turn-On Rise Time	t_r			3.5		
Turn-Off DelayTime	$t_{d(off)}$			19		
Turn-Off Fall Time	t_f			3.5		
Body Diode Reverse Recovery Time	t_{rr}	I_F= 8A, dI/dt= 500A/us	6		10	
Body Diode Reverse Recovery Charge	Q_{rr}		14		22	nC
Maximum Body-Diode Continuous Current	I_S				2.5	A
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V			1	V

Note.The static characteristics in Figures 1 to 6 are obtained using <300us pulses, duty cycle 0.5% max.

■ Marking

Marking	4818 KA****

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■ Typical Characterisitics

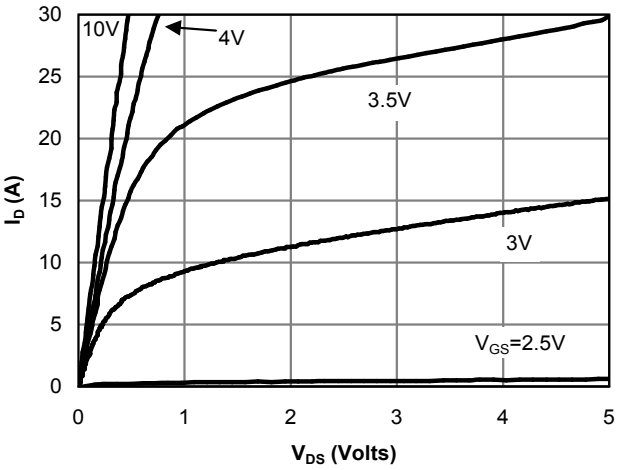

Fig 1: On-Region Characteristics (Note E)

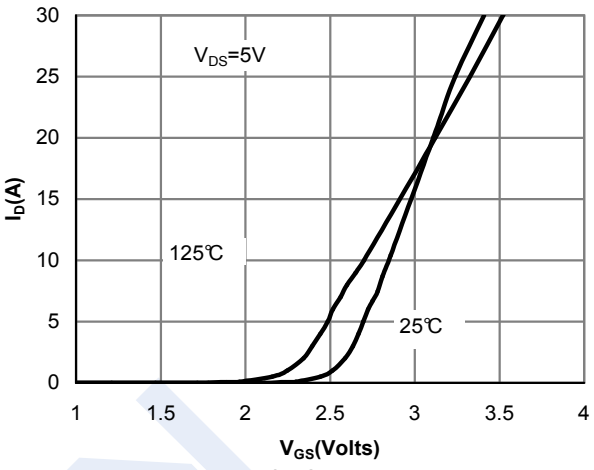

Figure 2: Transfer Characteristics (Note E)

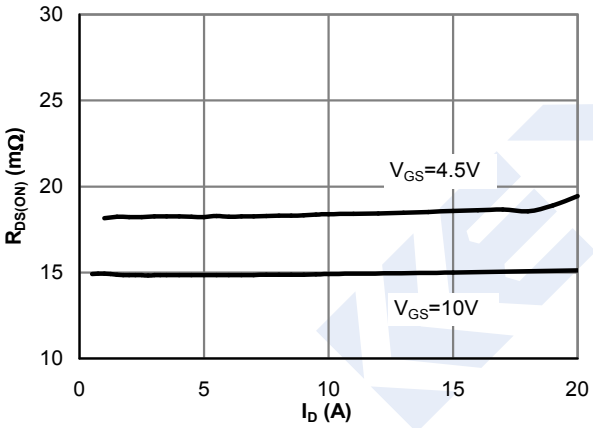

Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

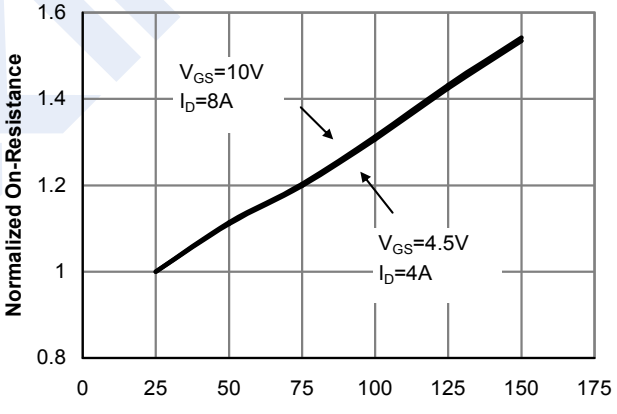

Figure 4: On-Resistance vs. Junction Temperature (Note E)

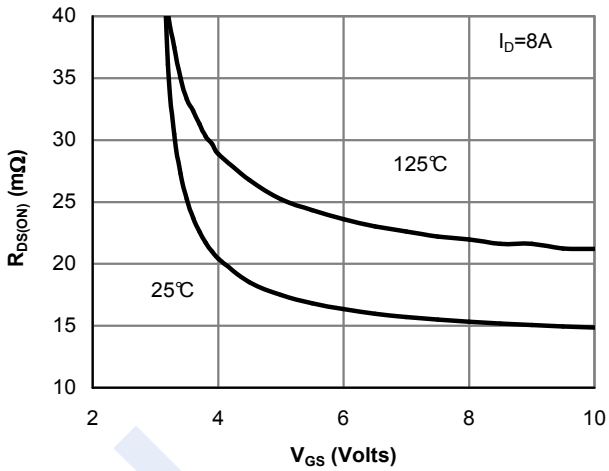

Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

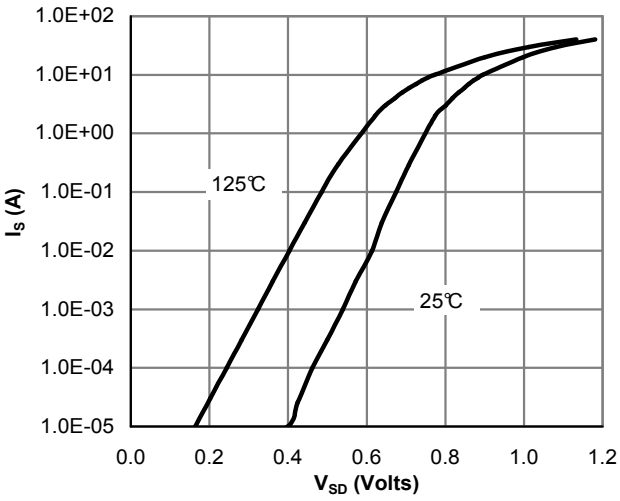

Figure 6: Body-Diode Characteristics (Note E)

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■ Typical Characterisitics

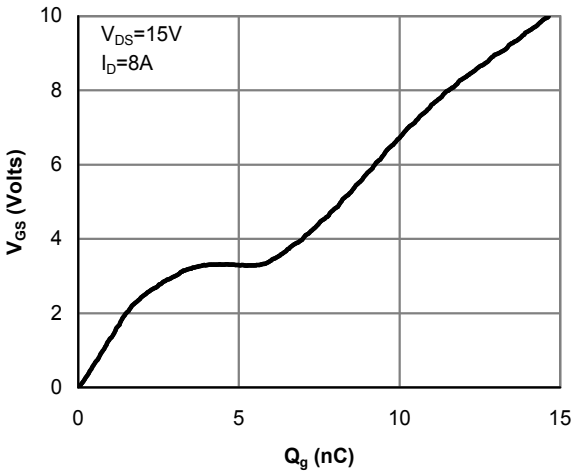

Figure 7: Gate-Charge Characteristics

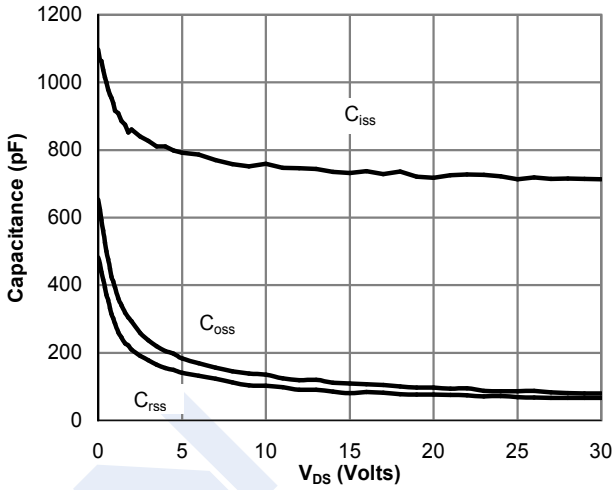

Figure 8: Capacitance Characteristics

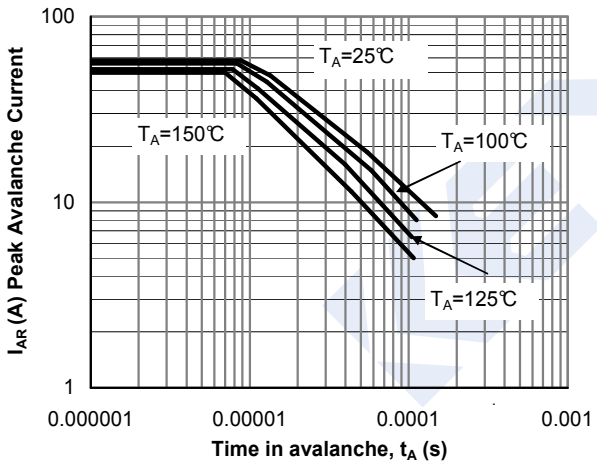

Figure 9: Single Pulse Avalanche capability (Note C)

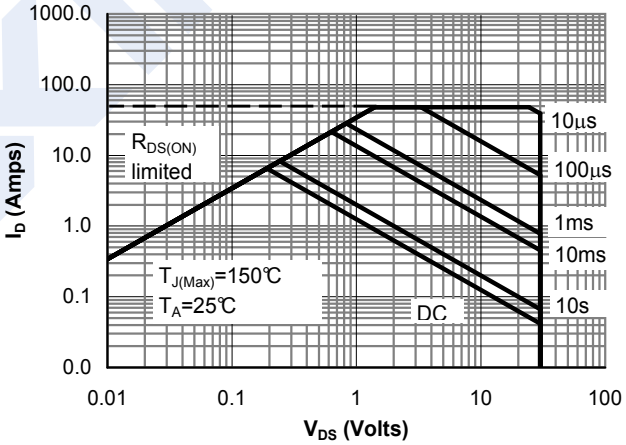

Figure 10: Maximum Forward Biased Safe Operating Area (Note F)

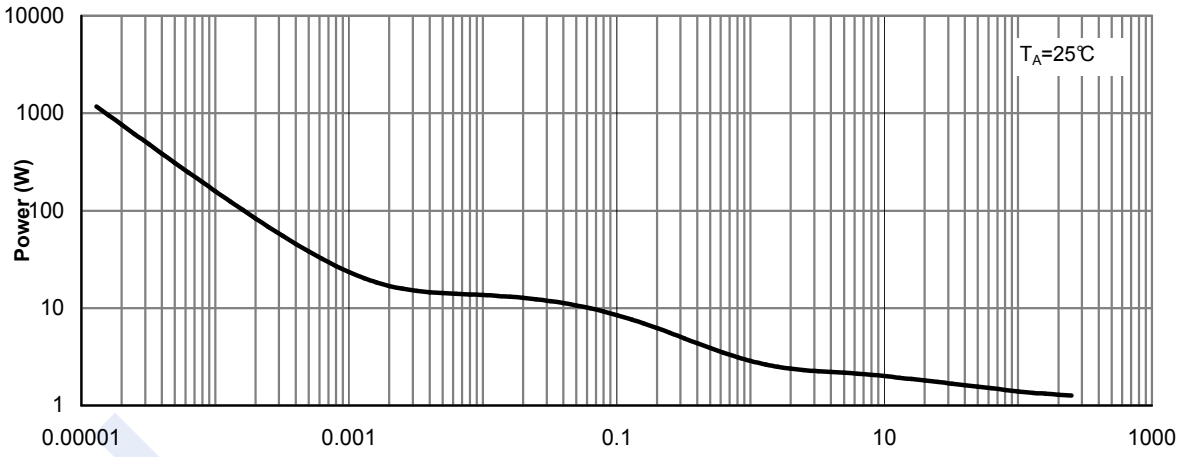

Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note F)

Dual N-Channel MOSFET

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■ Typical Characterisitics

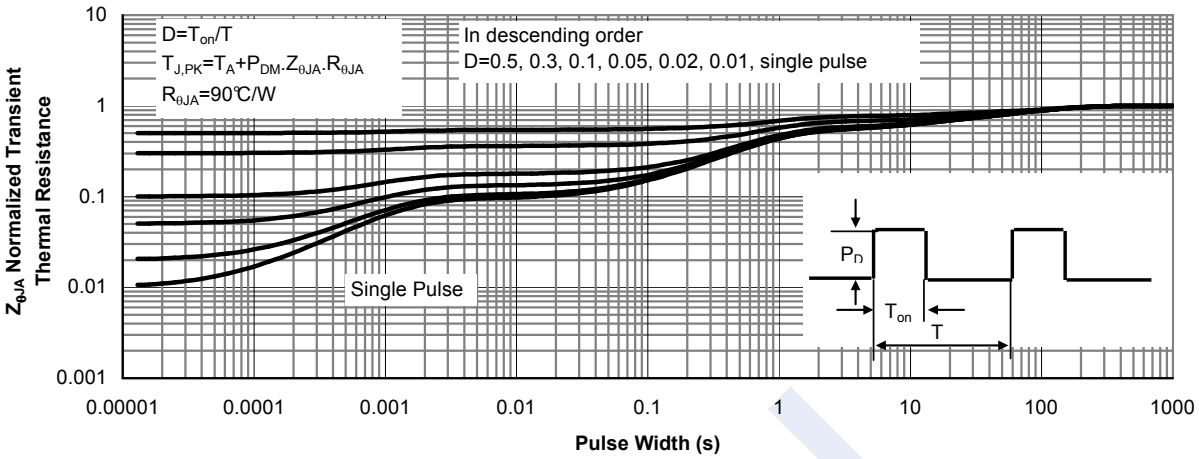

Figure 12: Normalized Maximum Transient Thermal Impedance (Note F)